

**Amendments to the Specification:**

**Beginning at page 1, line 2, please insert the following paragraph:**

**CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is a divisional application of U.S. Application Serial No. 09/918,547, filed on August 1, 2001, <sup>Pat. 6,703,245</sup> now allowed, which claims priority from, and is a continuation-in-part of, U.S. Application No. 09/880,089 (U.S. Patent Publication No. US-2002-0043662 A1), filed June 14, 2001, <sup>Pat. 6,828,587</sup> and which claims the benefit of a foreign priority application filed in Japan on August 2, 2000, as Serial No. 2000-234913. This application claims priority all of these applications, and all of these applications are incorporated by reference.

**Please replace the paragraph beginning at page 1, line 17 as with the following amended paragraph:**

A technique has been developed for manufacturing a thin film transistor (hereinafter referred to as TFT) from a semiconductor film that has a polycrystal structure (the film is hereinafter referred to as crystalline semiconductor film) and is formed on a glass, ~~[[quarts]]~~ quartz or other substrate. A TFT formed from a crystalline semiconductor film is applied to flat panel displays, typically, liquid crystal display devices, as measures for realizing high definition image display, and is applied to monolithic displays in which a pixel portion and an integrated circuit necessary to drive the pixel portion are formed on the same substrate, as measures for realizing it.

**Please replace the paragraph beginning at page 2, line 6 as with the following amended paragraph:**

A crystalline semiconductor film can have a polycrystal structure if it is obtained by subjecting an amorphous semiconductor film formed on a glass, ~~[[quarts]]~~ quartz or other substrate to heat treatment or laser light irradiation for crystallization. Crystallization is known to progress from a crystal nuclear spontaneously generated in the interface between the amorphous semiconductor film and the substrate. While crystal grains in a polycrystal